

Theoretical Study for realization of spintronics devices

Keywords: Magnetoresistance, Spin-orbit interaction, Surface/Interface, First-principles calculation

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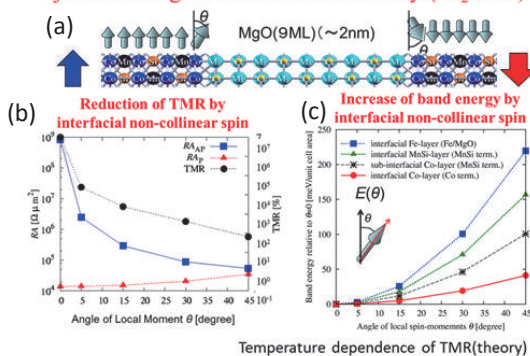


- Background**
- Large temperature dependence of magneto-resistance effects in experiments
 - Importance of interfacial spin-orbit interaction for functionality of spintronics devices
 - Importance of microscopic theory of thermal spin effects
 - Design of new materials for solving these problem

- Aim**
- Understanding of spin fluctuation effects on spin-dependent transport
 - Theoretical design of heterojunction interfaces developing giant spin-orbit interaction
 - Construction of microscopic theory for thermal spin effects
 - Machine learning studies for design of new spintronics materials

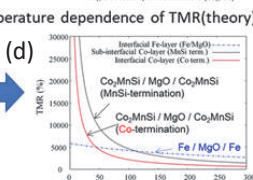
Advanced Research Topics

Temperature dependence of TMR of magnetic tunnel junction using half-metallic Heusler alloys (Co_2MnSi)



Large temperature dependence of tunnel magneto-resistance (TMR) using Heusler alloys

Importance of control for fluctuation of interfacial spin moment



(a) Model for $\text{Co}_2\text{MnSi}/\text{MgO}/\text{Co}_2\text{MnSi}$, (b) TMR v.s. angle of interfacial spin, (c) energy v.s. angle of interfacial spin, (d) calculation of temperature dependence of TMR

Publications

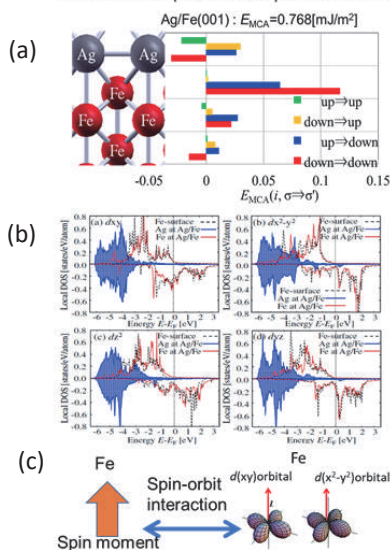
- Y. Miura et al., Phys. Rev. B **69**, 144413 (2004).
- Y. Miura, et al., Phys. Rev. B **83**, 214411 (2011).
- Y. Miura, et al., J. Appl. Phys. **113**, 233908 (2013).

Summary

- Spintronic device requires several physical properties such as large magnetoresistance, perpendicular magnetic anisotropy, low resistance.
- It is essential to control the magnetic properties at interfacial atomic layers from theoretical points of view.

Theoretical Study on magneto-crystalline anisotropy of Fe(001) interface

Contribution to magneto-crystalline anisotropy of interfacial atom (Second order perturbation analysis)



(a) Contribution of magneto-crystalline anisotropy of interfacial atom, (b) Local density of states of interfacial atoms, (c) relation between spin and orbital contributing perpendicular magnetic anisotropy

Research outcome

- Design of magnetic hetero junctions showing magnetoresistance ratio of more than 1000% at room temperature
- Design of heterojunction interface developing giant spin-orbit interaction
- Design of new materials showing huge thermal spin effects